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B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

January 2024 Semester End Main Examinations

Programme: B.E.

Branch: Electronics and Instrumentation Engineering

Course Code: 19EI7PCVID

Course: VLSI DESIGN

Semester: VII

Duration: 3 hrs.

Max Marks: 100

Instructions: 1. Answer any FIVE full questions, choosing one full question from each unit.
2. Missing data, if any, may be suitably assumed.

			UNIT - I			
			CO	PO	Marks	
Important Note: Completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. Revealing of identification, appeal to evaluator will be treated as malpractice.	1	a)	State Moore's Law with neat sketch and Explain Generations of an IC?	CO1	-	06
		b)	Discuss NMOS fabrication process with neat sketch	CO1	-	10
		c)	Compare Bipolar and CMOS Technologies	CO1	-	04
		OR				
	2	a)	Derive pull up to pull down ratio of an NMOS inverter driven through one or More pass transistor	CO2	PO1	10
		b)	List out and discuss alternative forms of pull-up transistor	CO2	PO1	06
		c)	Discuss NMOS inverter with neat sketch	CO1	-	04
		UNIT - II				
	3	a)	Obtain the scaling factor for the following parameter of a transistor a)Gate capacitance C_x b)Parasitic Capacitance C_x c)Saturation current I_{dss}	CO2	PO1	06
		b)	Construct two input nmos NAND and NOR gate stick Diagram.	CO2	PO1	06
		c)	With neat sketches, Discuss the lambda based design rules for wires, NMOS and CMOS transistor	CO2	PO1	08
		UNIT - III				
	4	a)	Design and implement Bus arbitration logic Using structured design along with stick diagram	CO3	PO3	08

	b)	What is parity generator and summarize briefly about structured design approach for the implementation of parity generator and also draw NMOS stick diagram for parity generator	CO3	PO3	08
	c)	Draw the General logic function block using two variable Technique.	CO2	PO1	04
UNIT - IV					
5	a)	Design four bit dynamic CMOS shift register using CMOS transmission gate switched logic and also draw the CMOS shift register cell.	CO4	PO3	10
	b)	Design and implement 4X4 barrel shifter circuit using 4x4 cross bar switch logic.	CO4	PO3	10
UNIT - V					
6	a)	Bring out a summative assessment of three transistor dynamic RAM cell in terms of Working, area occupied, dissipation and volatility	CO5	PO3	10
	b)	Implement and discuss optimization of CMOS inverter	CO5	PO3	10
OR					
7	a)	Implement and discuss NMOS and CMOS pseudo static Memory cell	CO5	PO4	10
	b)	Discuss the CAD tools used for design and simulation of a chip	CO5	PO4	10
